2SD0966 (2SD966)

Silicon NPN epitaxial planar type

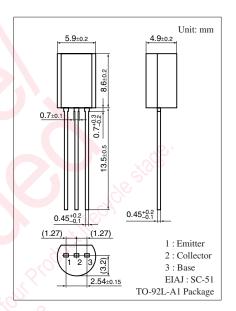
For low-frequency amplification For stroboscope

■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- Satisfactory operation performances at high efficiency with the lowvoltage power supply.

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|------------------|-------------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | 40 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 7 | V |
| Collector current | I_{C} | 5 | A |
| Peak collector current | I_{CP} | 8 | A |
| Collector power dissipation | P _C | 1 | W |
| Junction temperature | T _j | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °CO |



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|---|-----|-----|-----|------|
| Collector-emitter voltage (Base open) | V _{CEO} | $I_C = 1 \text{ mA}, I_B = 0$ | 20 | 35 | | V |
| Emitter-base voltage (Collector open) | $V_{\rm EBO}$ | $I_E = 10 \mu A, I_C = 0$ | 7 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 10 \text{ V}, I_{E} = 0$ | 0.7 | | 0.1 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 7 \text{ V}, I_{C} = 0$ | | | 0.1 | μΑ |
| Forward current transfer ratio *1 | h _{FE1} *2 | $V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$ | 180 | | 600 | _ |
| | h _{FE} | $V_{CE} = 2 \text{ V}, I_{C} = 2 \text{ A}$ | 150 | | | |
| Collector-emitter saturation voltage *1 | V _{CE(sat)} | $I_C = 3 \text{ A}, I_B = 0.1 \text{ A}$ | | | 1 | V |
| Transition frequency | f_T | $V_{CB} = 6 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | | 50 | pF |
| (Common base, input open circuited) | | X. | | | | |

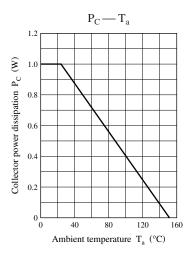
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

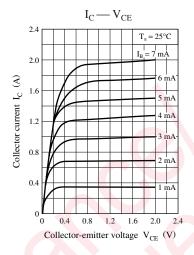
2. *1: Pulse measurement

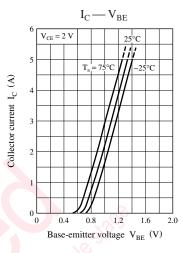
*2: Rank classification

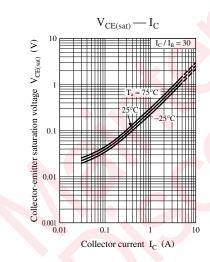
| Rank | Р | Q | R |
|------------------|------------|------------|------------|
| h _{FE1} | 180 to 270 | 230 to 380 | 340 to 600 |

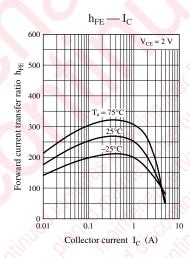
Note) The part number in the parenthesis shows conventional part number.

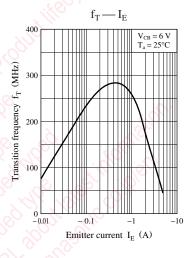


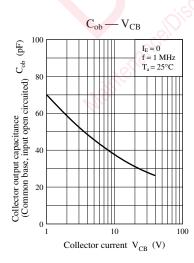












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